

# Laser-Plasma Doping as A Tool for Material Research: From Quantum Emitters to Superconducting Diamond

JLF user meeting February 12, 2025

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# Team



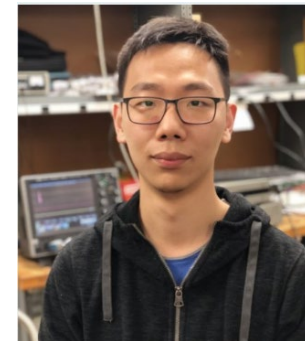
Arun  
Persaud



Kaushalya  
Jhuria



Wei  
Liu



Xinran  
Li



Amanda  
Hebert



Thomas  
Schenkel

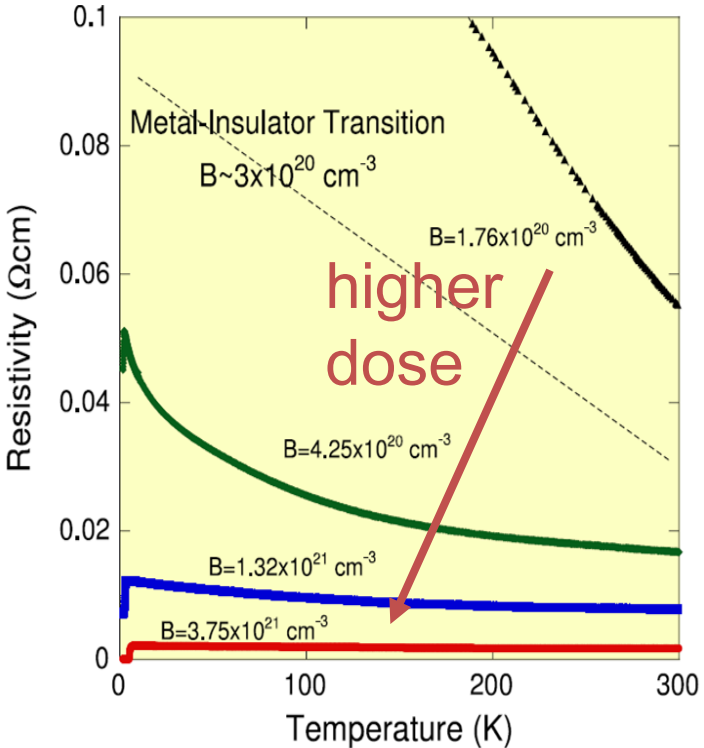


<https://atap.lbl.gov>

Fusion Science and  
Ion Beam Technology Group

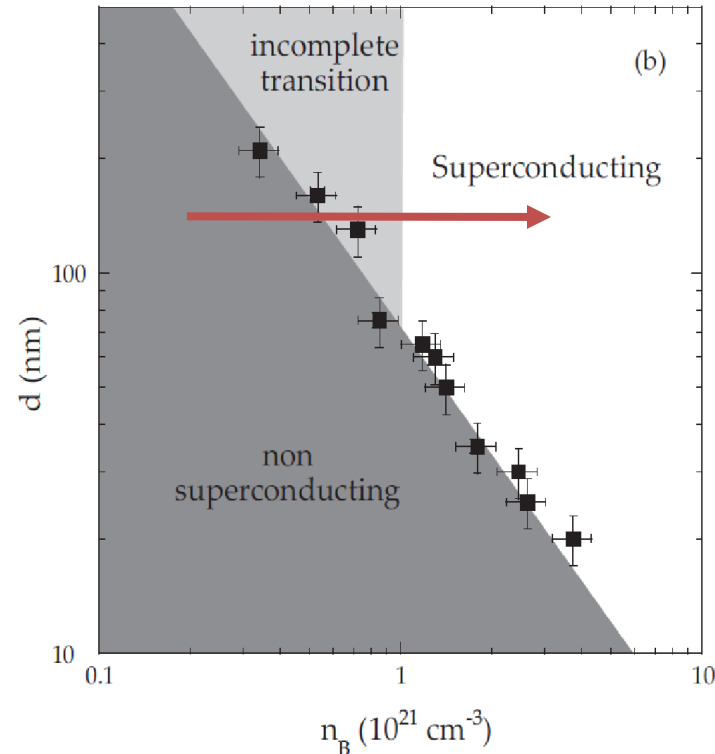
# Superconductivity in boron-doped diamond

Y. Takano, J. Phys. Condens. Matter **21** 253201 (2009)



Temperature versus resistivity of Diamond at different Boron concentrations

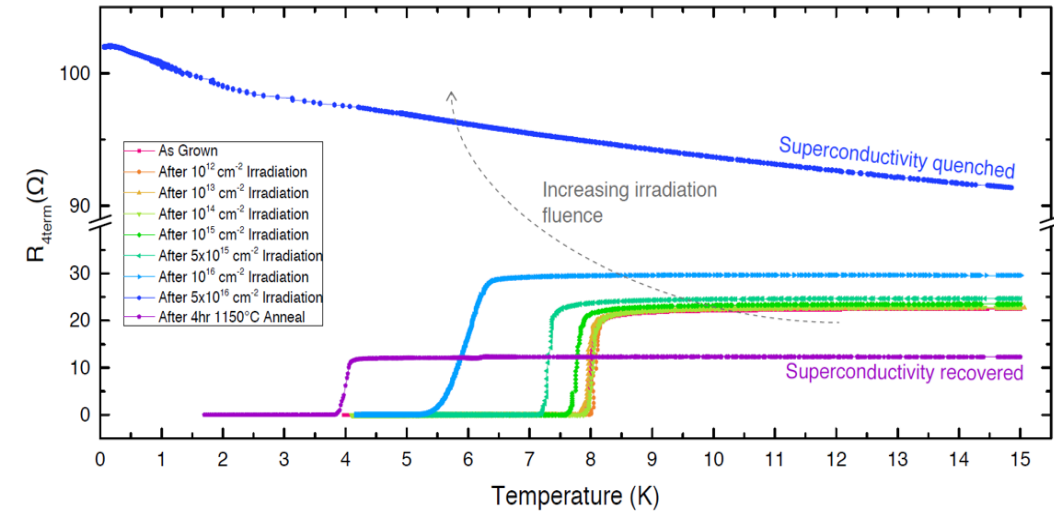
A. Grockowiak, et al., Phys. Rev. B **88**, 064508 (2013)



Boron shows similar behaviour as silicon

$T_c$  of  $\sim 10K$  for diamond has been reported with boron incorporation from growth.

D. L. Creedon, et al., Phys. Rev. Applied **10**, 044016

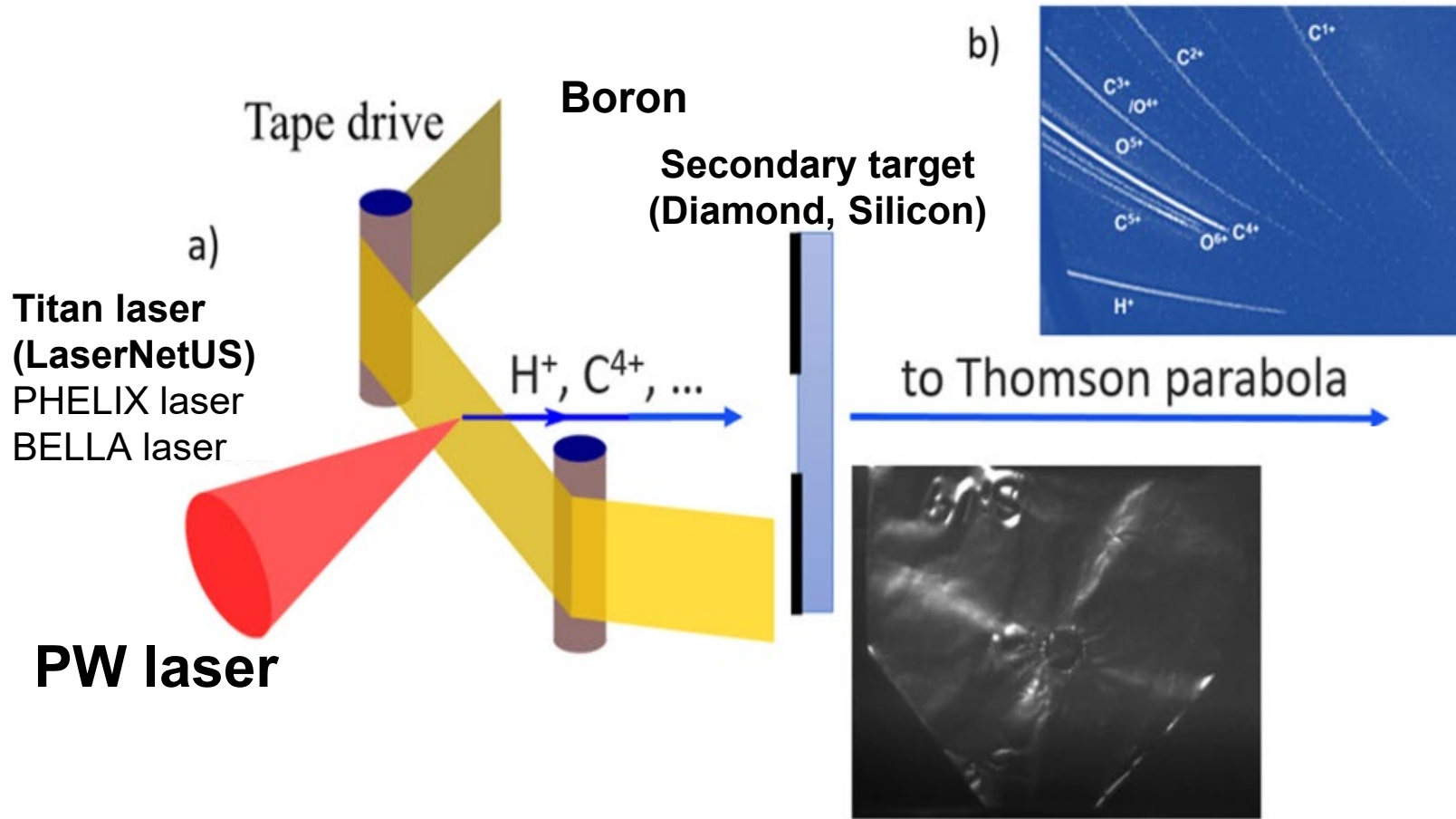


Superconductivity is hindered and quenched post-conventional ion implantation due to the high crystal damage

Critical temperature  $T_c$  of up to 50K is theoretically predicted for boron-doped diamond

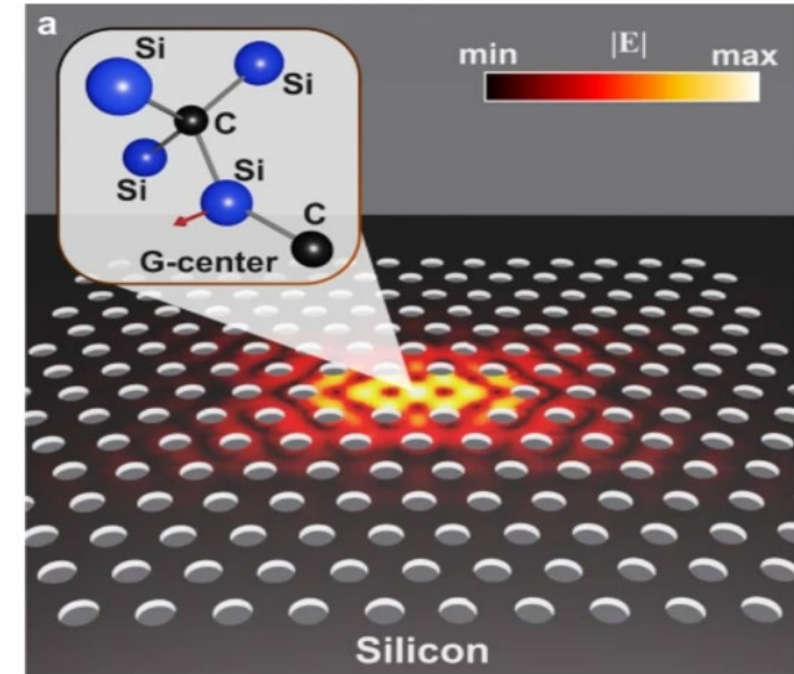
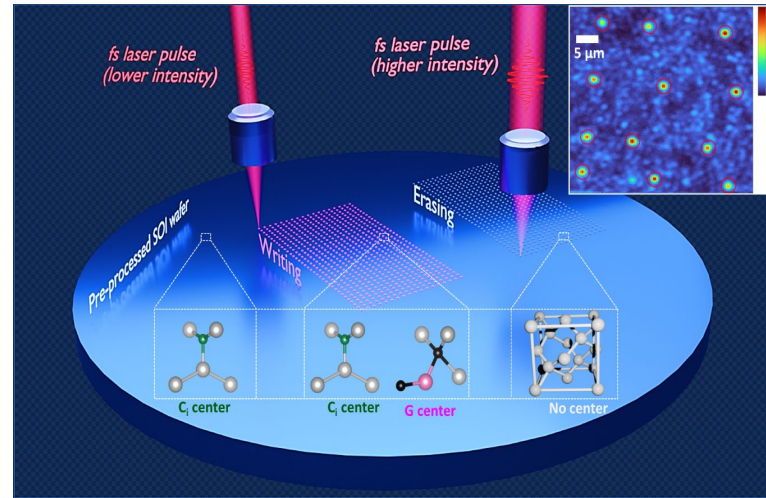
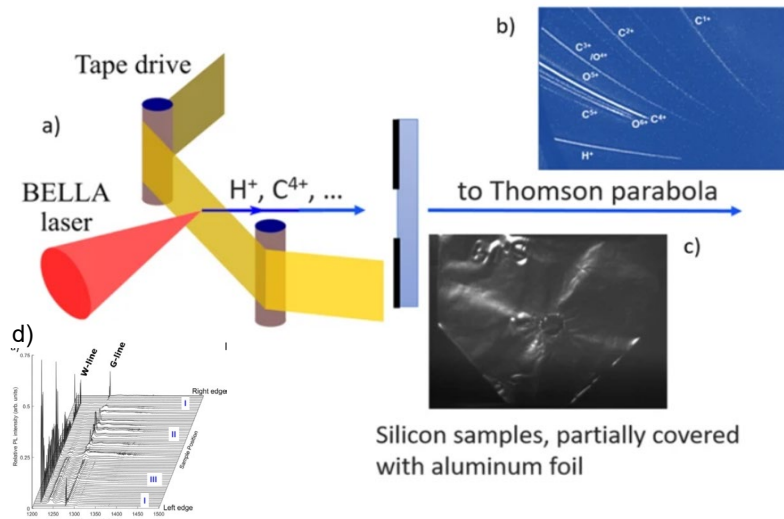
Moussa, Cohen, Phys. Rev. B Condens. Matter Mater. Phys. **77**, 064518 (2008)

# We use laser-driven ion acceleration to create intense ion beams



Redjem, W., *et al.*, Defect engineering of silicon with ion pulses from laser acceleration. *Comm. Mater.* **4**, 22 (2023)

# We also make high-quality spin-photon qubits using conventional and non-conventional methods



**Schematic of the tape drive and ion target assembly with the secondary target to implant hydrocarbons into silicon and form telecom band color centers**

**Artistic representation of the fs laser irradiation approach to locally write and erase G, and  $C_i$  centers in SOI.**

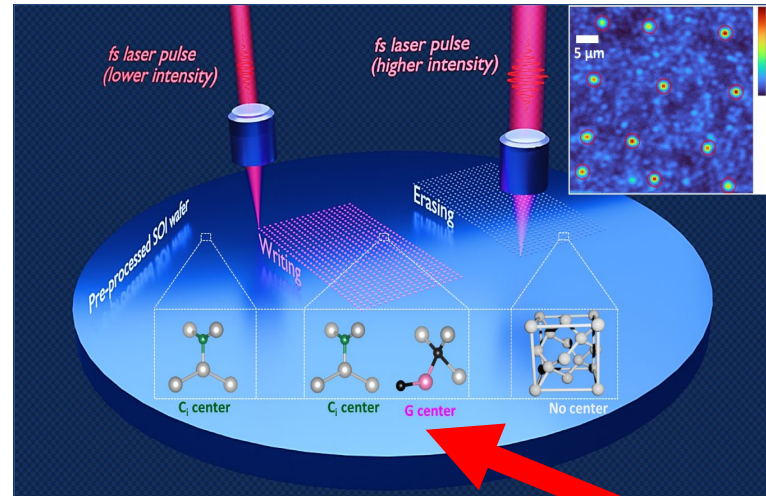
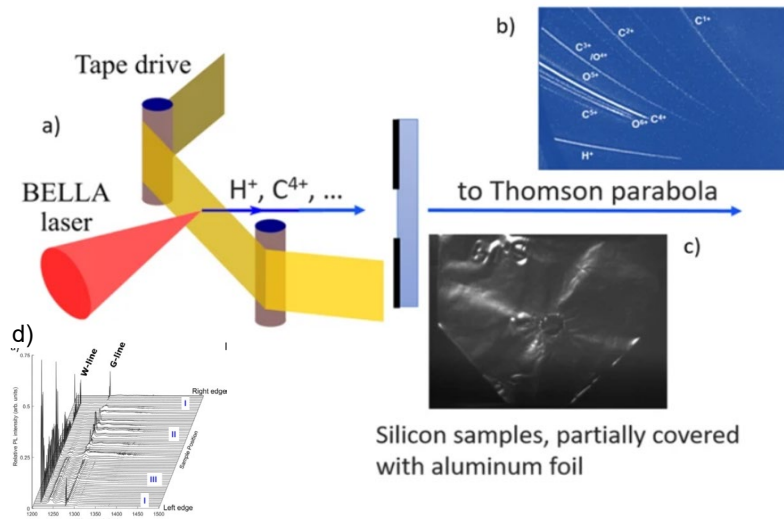
**A single atomic emissive center embedded in a silicon-photonic cavity.**

Redjem, W., *et al.* Defect engineering of silicon with ion pulses from laser acceleration. **Comm. Mater.** **4**, 22 (2023)

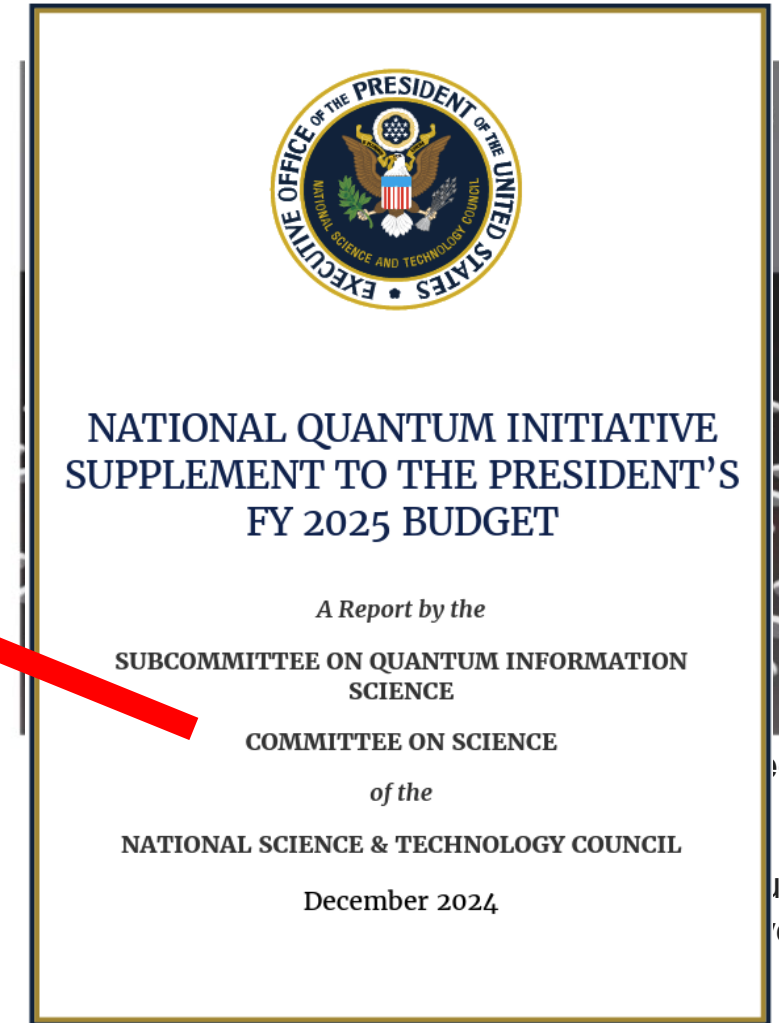
Jhuria, K., Ivanov, V., Polley, D. *et al.* Programmable quantum emitter formation in silicon. **Nat. Comm.** **15**, 4497 (2024)

Redjem, W., K.Jhuria, *et al.* All-silicon quantum light source by embedding an atomic emissive center in a nanophotonic cavity. **Nat. Comm.** **14**, 3321 (2023).

# We also make high-quality spin-photon qubits using conventional and non-conventional methods



Artistic representation of the fs laser irradiation approach to locally write and erase G, and  $C_i$  centers in SOI.



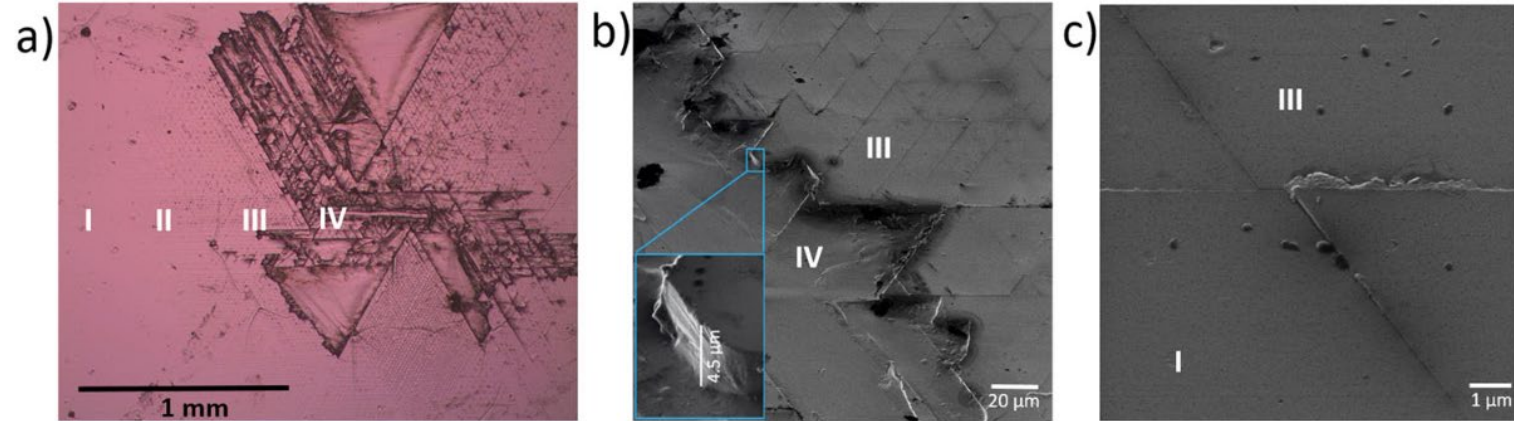
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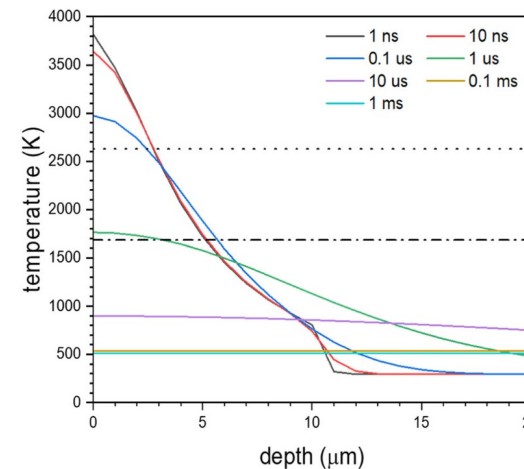
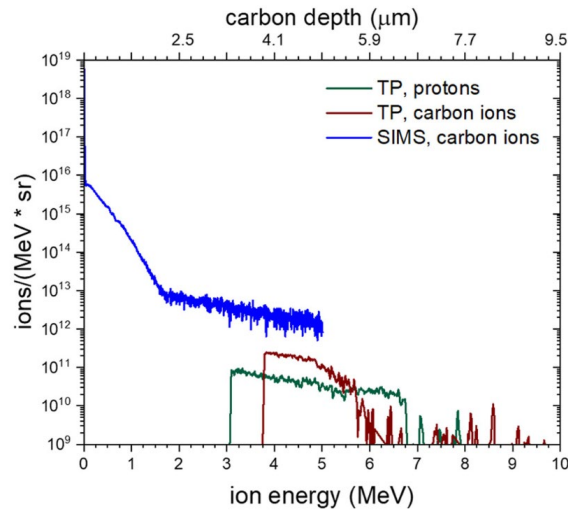
Jhuria, K., Ivanov, V., Polley, D. *et al.* Programmable quantum emitter formation in silicon. *Nat. Comm.* **15**, 4497 (2024)

# Laser ion implantation is a unique tool to provide high fluxes and high temperatures

Microscope images of ion beam hits (images from Si sample)



Ion energy distribution from TP and SIMS



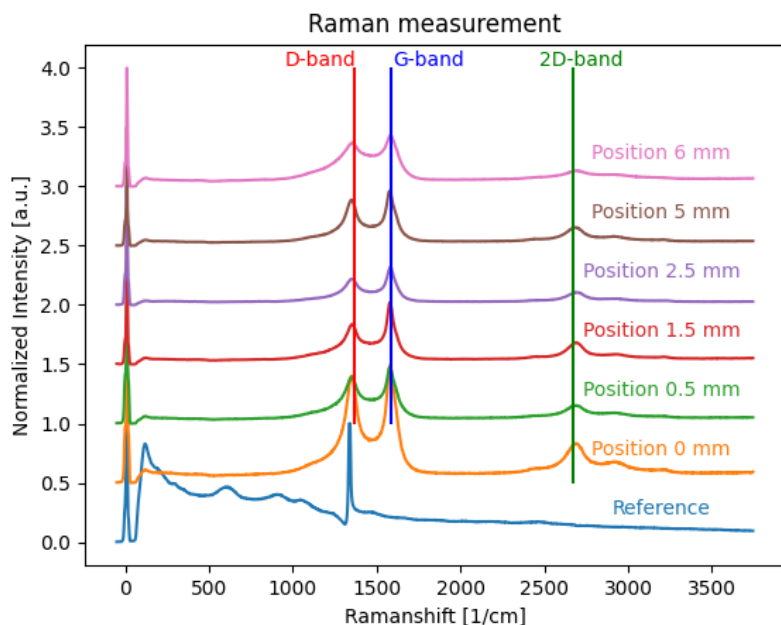
Simulated temperature distribution as a function of time

Redjem, W., et al., Defect engineering of silicon with ion pulses from laser acceleration. *Commun. Mater.* **4**, 22 (2023)

# Ex-situ material characterization for electrical and structural properties of boron-doped diamond

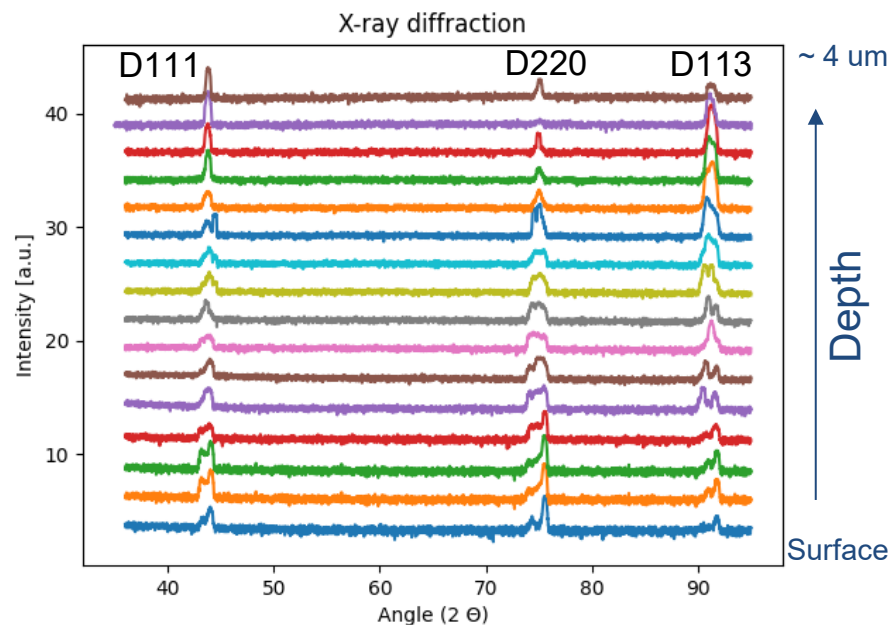
## Raman spectroscopy

Raman spectroscopy helps us understand the structural properties of boron doped diamond and their impact on the superconducting phase



## X-Ray diffraction

Depth-resolved X-ray diffraction analysis helps us understand the structural properties of diamond post laser-ion doping



(Measurements done at RT)

## Hall effect

Hall measurement measures RT mobility and carrier concentration.

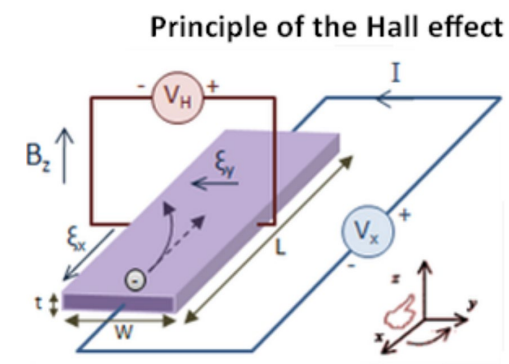
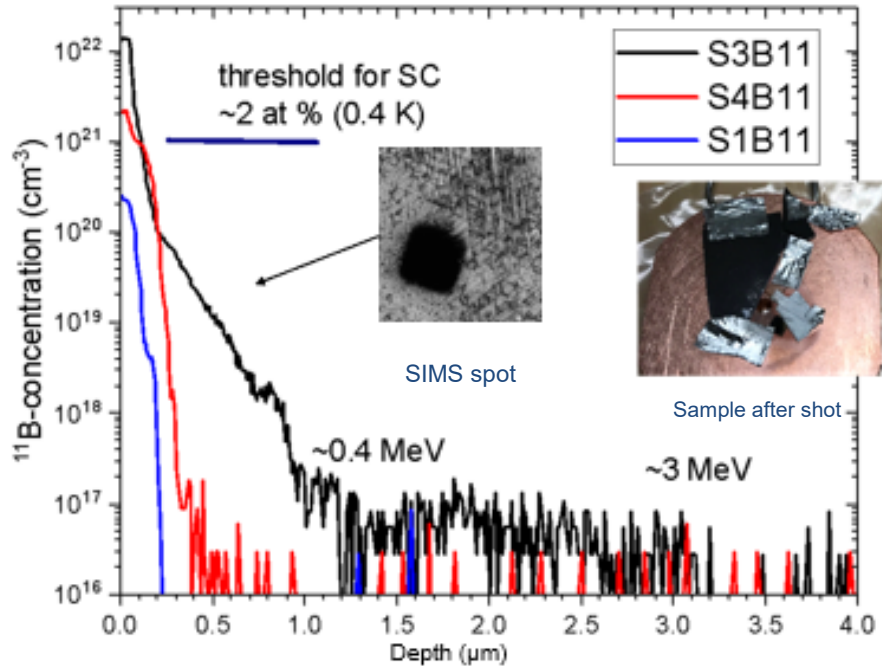


Image taken from <https://www.testandmeasurementtips.com/measuring-the-hall-effect-faq/>

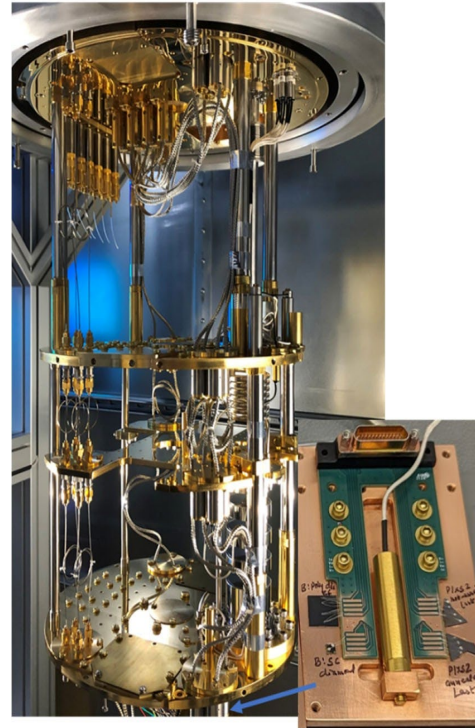


# First demonstration of superconductivity in boron-doped diamond post ion implantation

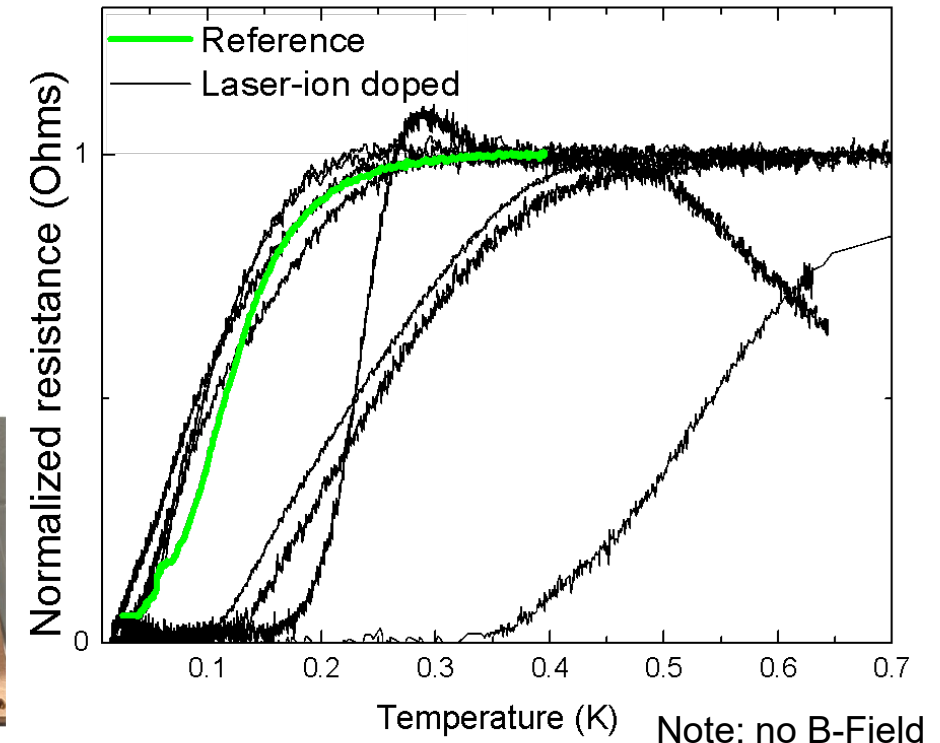
Doping profile shows high concentrations      Low-temperature transport measurement show superconductivity



SIMS profile shows concentration well above metal-insulator transition post laser ion doping (data from Si sample)



Cryostat used for SC measurements

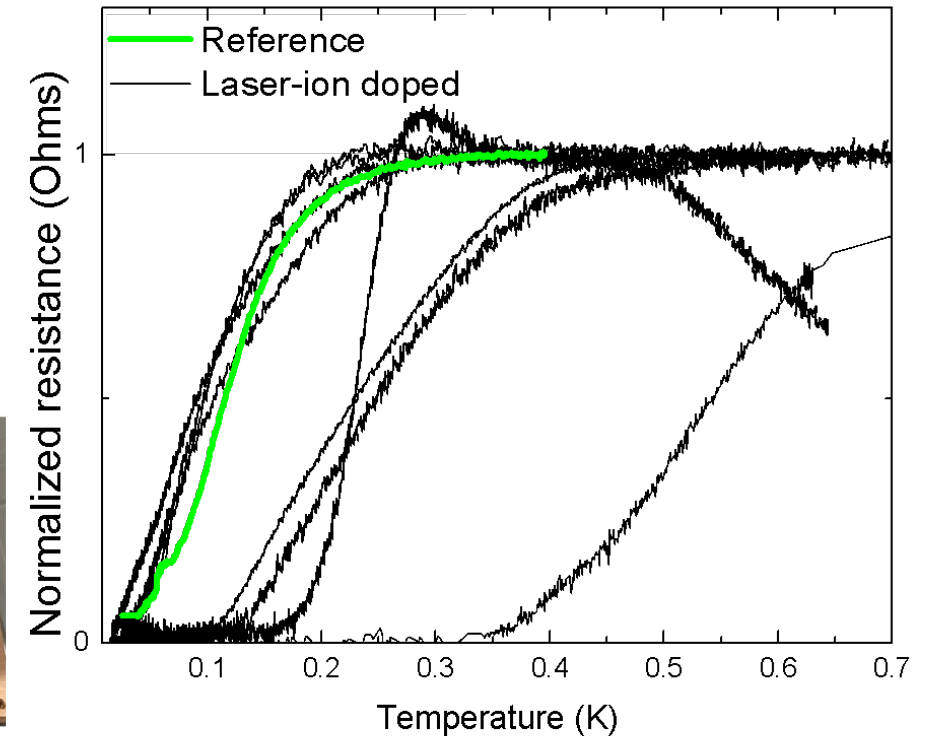
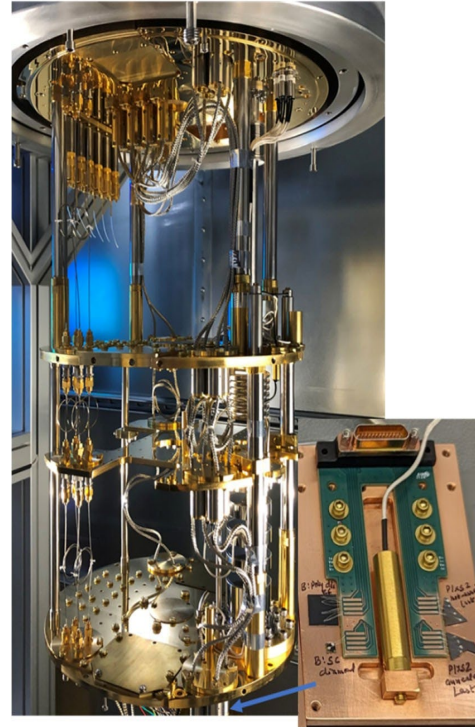
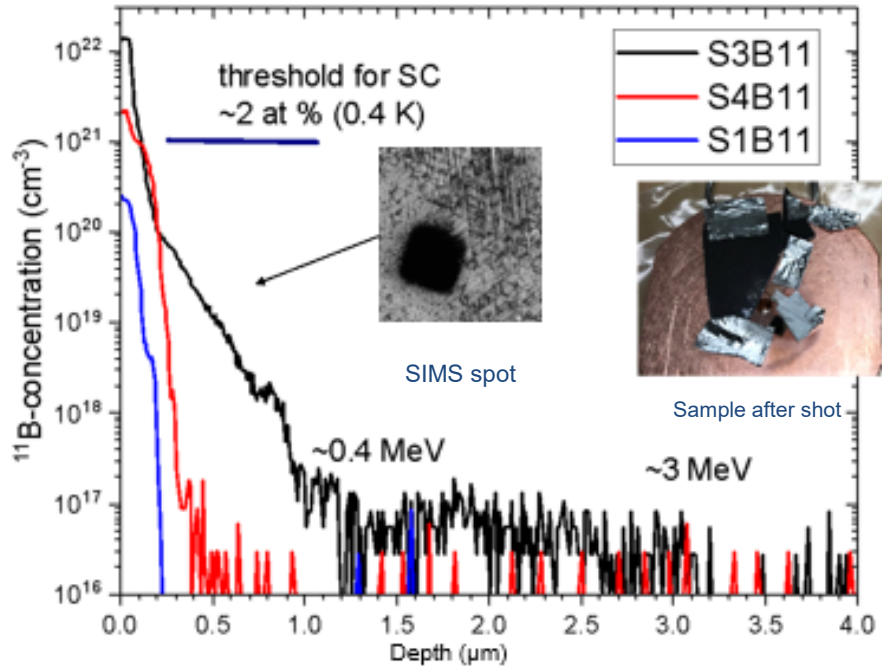


(Reference sample is boron doped diamond sample where  $2 \times 10^{20}$  B/cm<sup>2</sup> was introduced during growth showing partial transition to superconductivity)

K. Jhuria, *et al.*, Non-trivial superconducting phase in Boron doped polycrystalline diamond (manuscript under preparation)

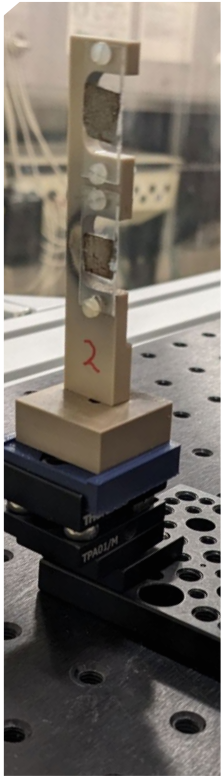
# First demonstration of superconductivity in boron-doped diamond post ion implantation

Doping profile shows high concentrations      Low-temperature transport measurement show superconductivity

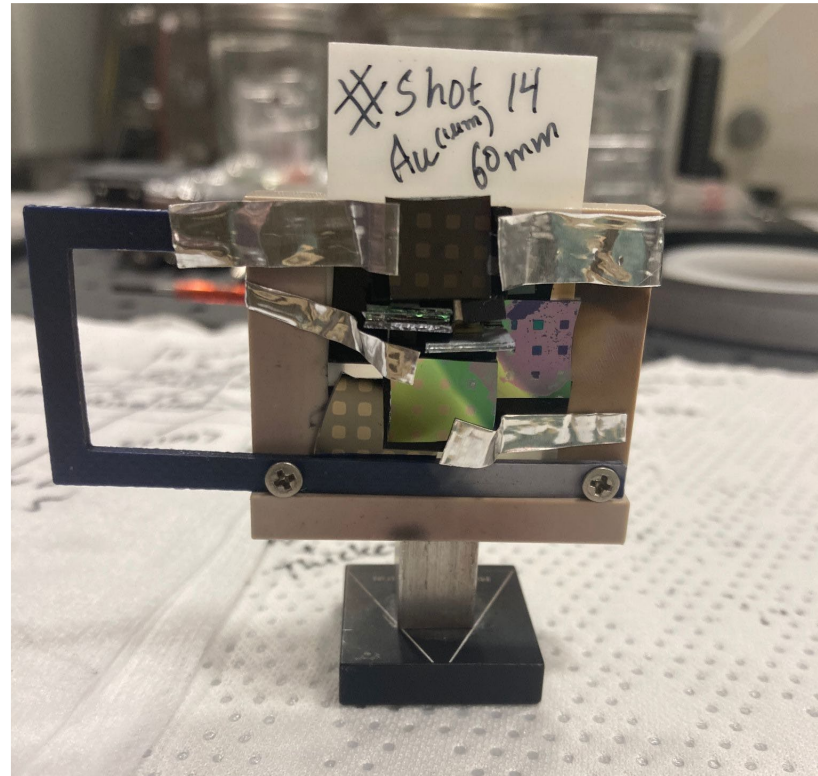


Summary: Unique beam qualities of laser accelerated ions allows us to create material properties that cannot be achieved using standard implantation techniques

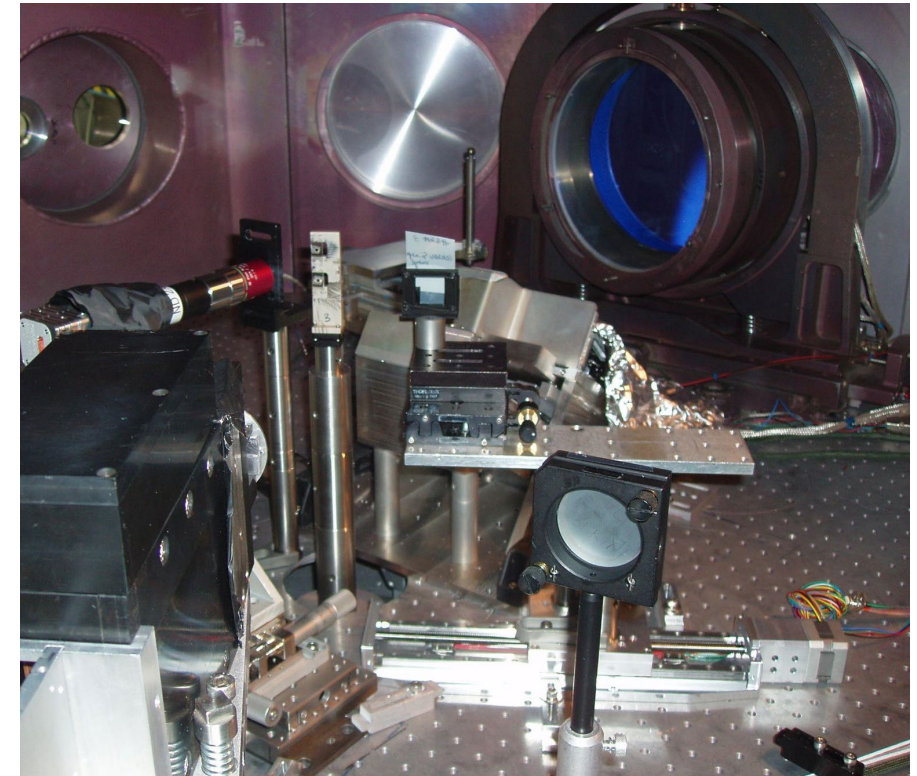
# Typical setup for our laser-plasma ion-doping experiments



Sample holder for laser target foils

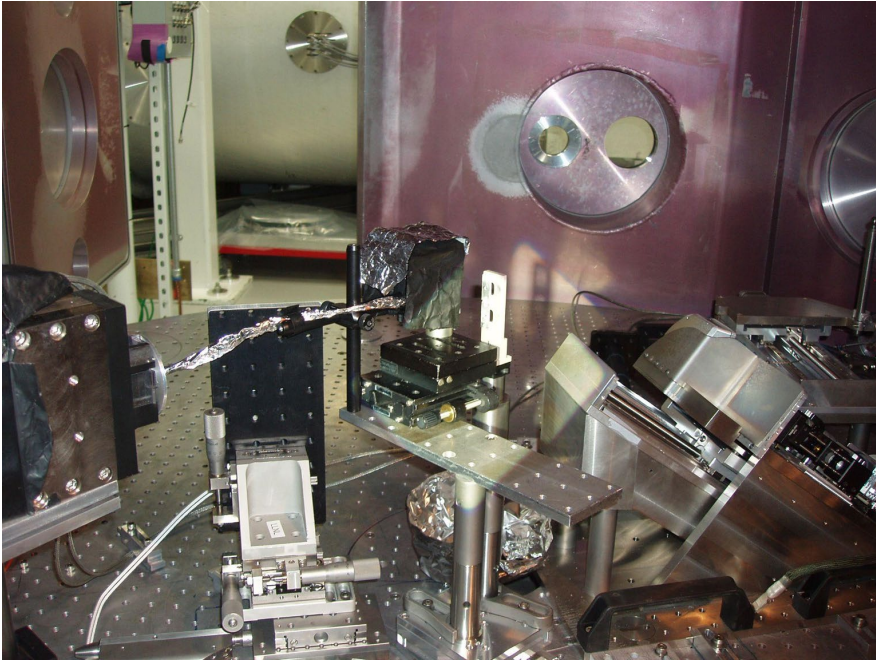


Sample holder for implantation targets

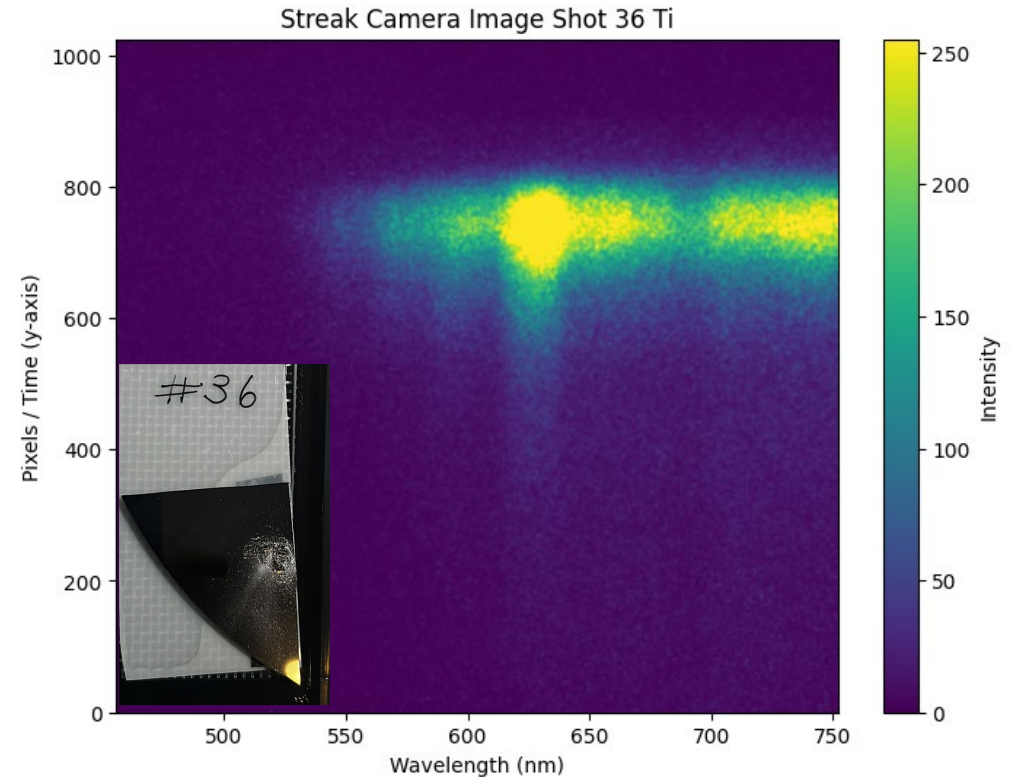


Target chamber at Titan

# Started to test streak camera images for in-situ diagnostics

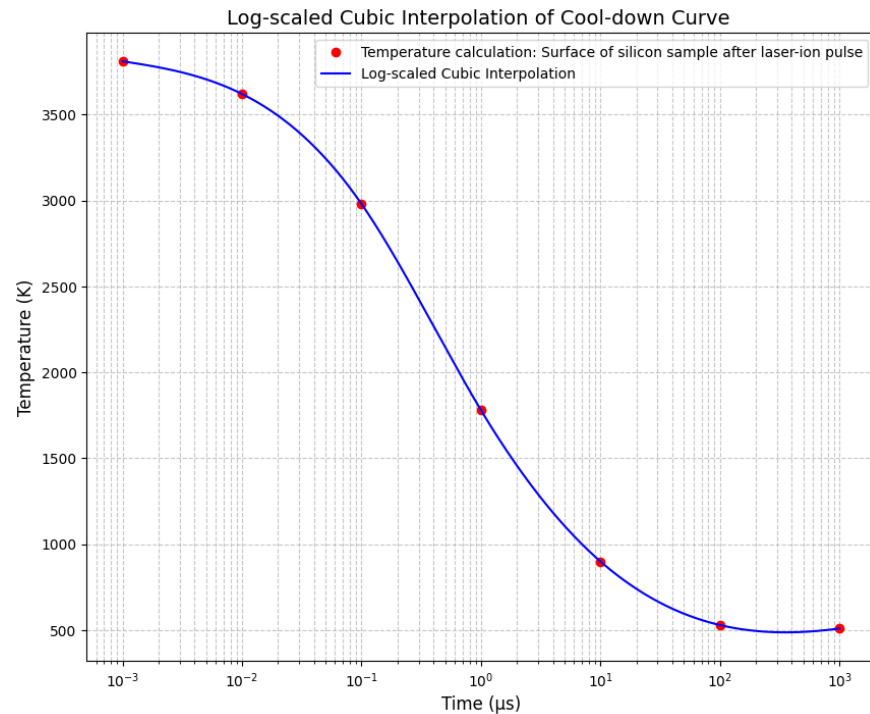


Streak camera setup in the chamber. Here, the fiber is pointed at the backside of the secondary target.



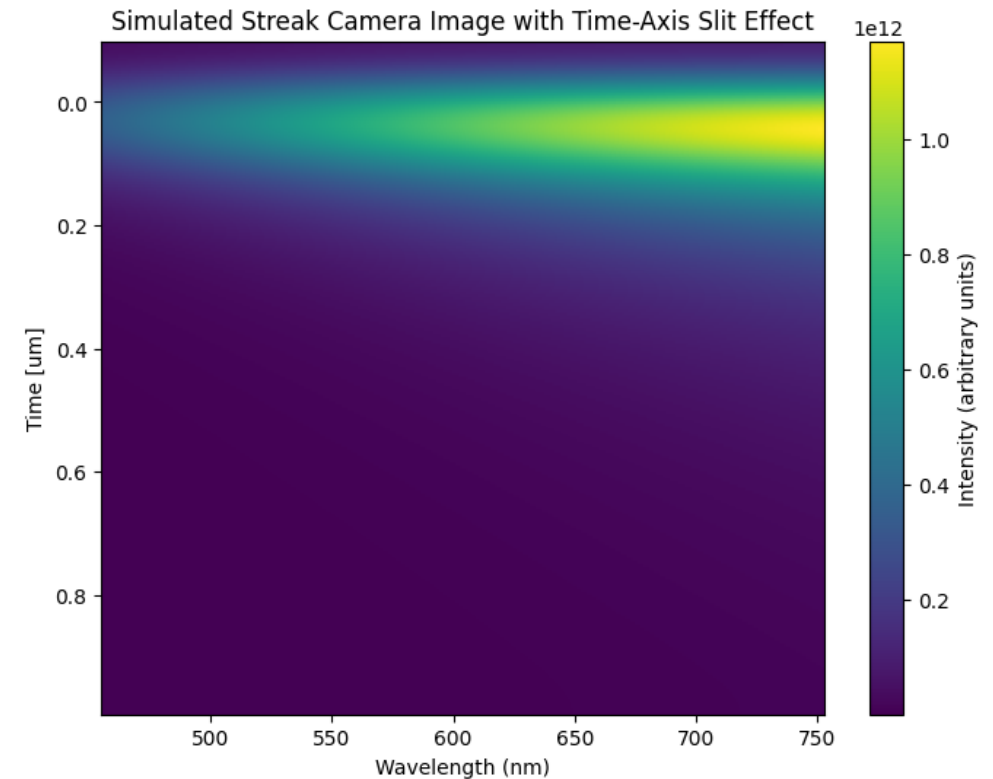
Streak camera image taken of front of intrinsic silicon (secondary target) for a titanium shot (primary target). Time delays were adjusted using the 5 Hz laser and a delay generator relative to the main trigger. (dt: 2  $\mu$ s)

# First Streak Camera images to measure temperature profiles



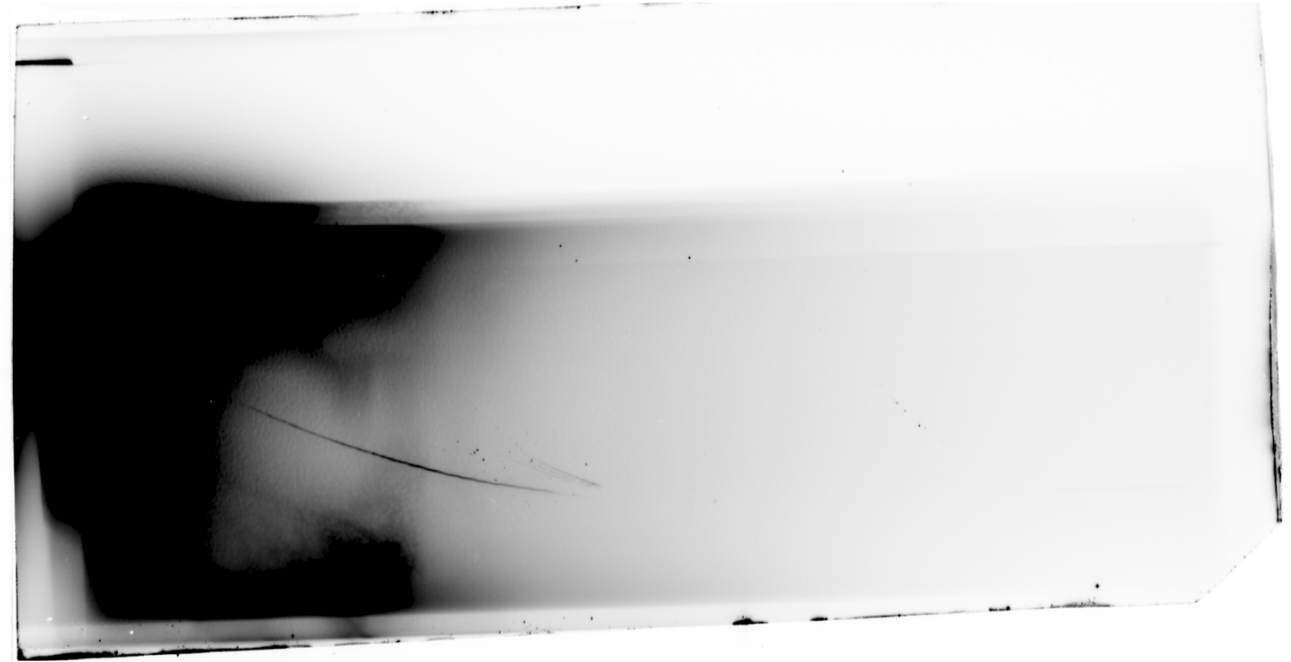
Simulated temperature profile using energy deposition during laser-plasma implantation.

Redjem, W., Amsellem, A.J., Allen, F.I. *et al.* Defect engineering of silicon with ion pulses from laser acceleration. *Commun Mater* **4**, 22 (2023). <https://doi.org/10.1038/s43246-023-00349-4>



Preliminary simulation of black body radiation using the temperature profile on the left shows reasonable agreement.

# Mixed results from Thomson Parabola shots taken during Titan run



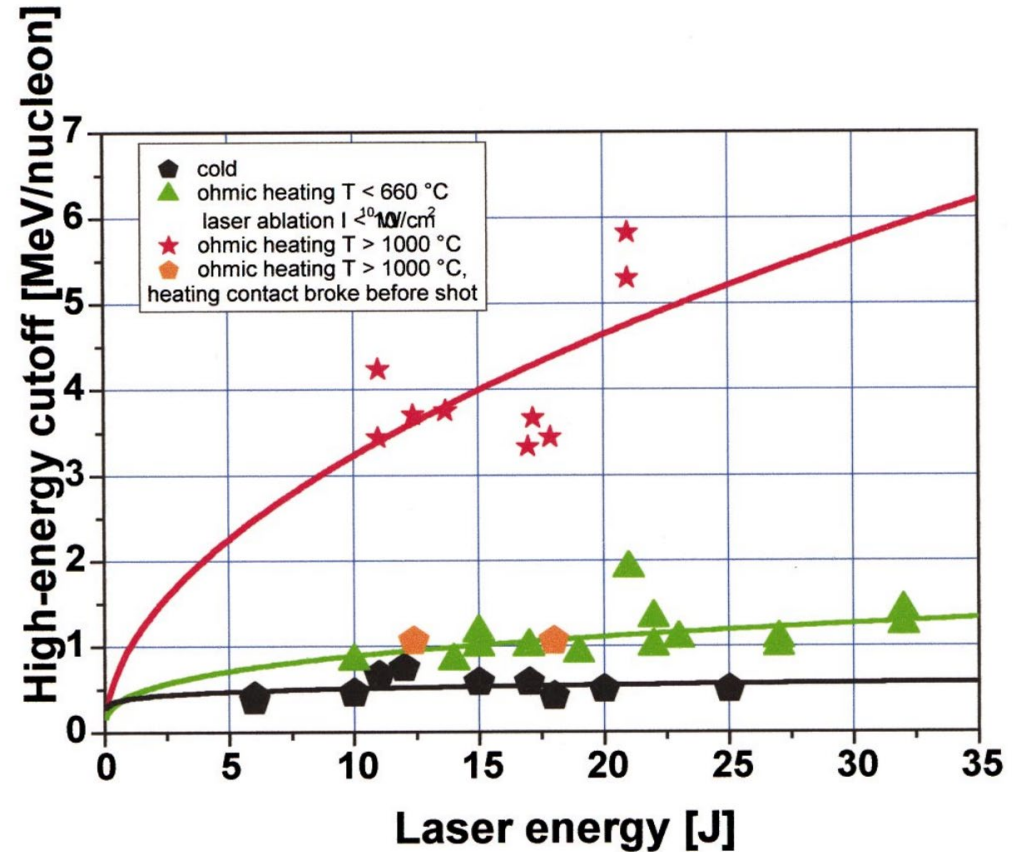
Thomson parabola from Al shot left and Cu/Ni right. (Shot 8 and 21) show separate parabolas from different ion species and charge states.

However, the right shot shows also typical noise that we have seen in many shots. Sometimes the noise covers the whole region of interest.

# Outlook: Pre-cleaning the target foil is an interesting option for us to reduce implantation of unwanted species

Pre-clean of foil to reduce H, C, and O ions.  
Several options to achieve pre-cleaning:

- Radiative heating
- CW laser heating (attempted with defocused CW last beamtime)
- Ohmic/resistive heating
- Short pulse laser ablation
- Ion etching



B. M. Hegelich, et al.; *Phys. Plasmas* 1 May 2005; 12 (5): 056314. <https://doi.org/10.1063/1.1915350>

# Outlook

- Data analysis ongoing from a successful LaserNet US beamtime
- More measurements at LaserNet Us facilities planned
- Working on better ion beam diagnostics to correlate beam conditions with samples conditions (including Thomson parabola and Streak cameras)
- Move to thinner diamond films, for improved superconductivity measurements
- *In-situ* cleaning of foils before laser shot to remove O, C, H contaminants
- Preparing structures on samples, e.g., for single photon detector (detect change from SC to non-SC when a photon hit)





# Thank you for your attention!

## Questions?

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The presented results are based on experiments conducted at the Jupiter Laser Facility (LLNL, Livermore, USA) through LaserNetUS and at the PHELIX facility (GSI Helmholtzzentrum für Schwerionenforschung, Darmstadt, Germany).

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